N-CHANNEL ENHANCEMENT MODE POWER MOSFET

TF80N03

● General Description

The TF80N03 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$ .This device is ideal for load switch and battery protection applications.

● Features

Advance high cell density Trench technology

Low $R_{DS(ON)}$ to minimize conductive loss

Low Gate Charge for fast switching

Low Thermal resistance

●Application

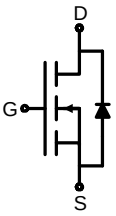
MB/VGA Vcore

SMPS 2nd Synchronous Rectifier

POL application

BLDC Motor driver

● Product Summary



V_{DS} =30V I_D=80A

$R_{DSON(10V\ typ)}$ =3.9mΩ

$R_{DSON(4.5V\ typ)}$ =6.3mΩ

RoHS compliant

TO-251

TO-252

●Ordering Information:

Part NO.	TF80N03
Marking 1	TF:tuofeng;80N03:TF80N03
Marking 2	YY:year code; XX:Week; AA:device code;
MOQ	TO-251:50/PCS TO-252:2500/PCS

●Absolute Maximum Ratings (T_C =25℃)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	$I_{D@}T_C$=25℃	80	A
	$I_{D@}T_C$=75℃	60	A
	$I_{D\ @}T_C$=100℃	48	A
Pulsed Drain Current ①	I_{DM}	280	A
Total Power Dissipation	$P_D@T_C$=25℃	46	W
Total Power Dissipation	$P_D@T_A$=25℃	2.0	W
Operating Junction Temperature	T_J	-55 to 150	℃
Storage Temperature	T_{STG}	-55 to 150	℃

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Single Pulse Avalanche Energy	E_{AS}	150	mJ
Avalanche Current	I_{AS} I_{AR}	30	A

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.7	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	55	° C/W
Soldering temperature, wave soldering for 8s	T_{sold}	-	-	265	° C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V,I_D =250uA	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =250uA	1.0	1.7	2.5	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=30V, V_{GS} =0V			1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V ,V_{DS} =0V			±100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=30A		3.9	5.0	mΩ
		V_{GS}=4.5V, I_D=20A		6.3	8.5	mΩ
Forward Transconductance	g_{FS}	V_{DS} =15V, I_D=20A		15		S
Source-drain voltage	V_{SD}	Is=30A			1.20	V

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	Ciss	Vds=15V,Vgs=0V f = 1MHz	-	1616	-	pF
Output capacitance	Coss		-	245	-	
Reverse transfer capacitance	Crss		-	216	-	

●Gate Charge characteristics(T_a = 25℃)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Risistance	R_g	f = 1MHz		1.50		Ω
Total gate charge	Qg	V_{DD} = 15V	-	33.5	-	nC
Gate - Source charge	Qgs	I_D = 30A	-	8.50	-	
Gate - Drain charge	Qgd	V_{GS} = 10V	-	7.50	-	
Turn-ON Delay time	$t_{D(on)}$	V_{GS}=10V ,V_{DS}=15V R_G =3.0Ω, I=30A		7.50		ns
Turn-ON Rise time	t_r			14.5		ns
Turn-Off Delay time	$t_{D(off)}$			35.0		ns
Turn-Off Fall time	t_f			9.50		ns

Fig.1 Power Dissipation

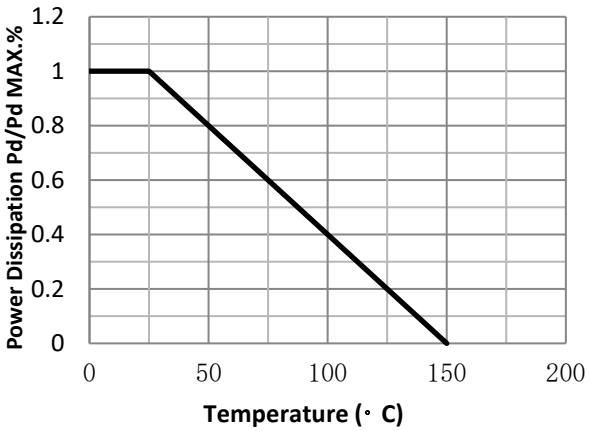


Fig.2 Typical output Characteristics

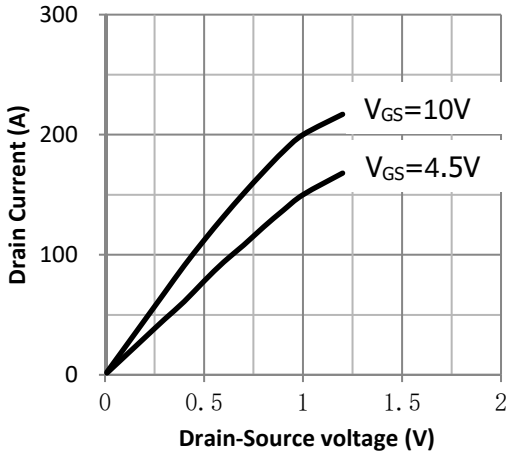


Fig.3 Threshold Voltage V.S Junction Temperature

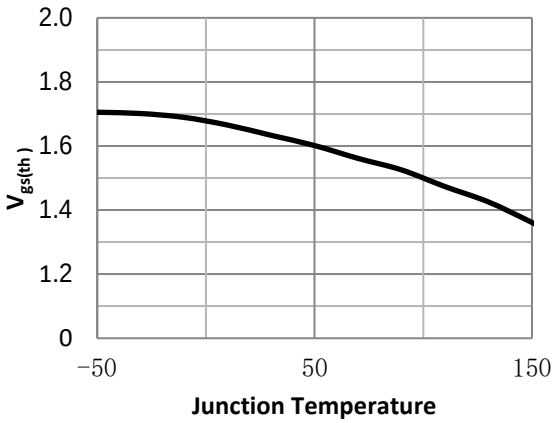


Fig.4 Resistance V.S Drain Current

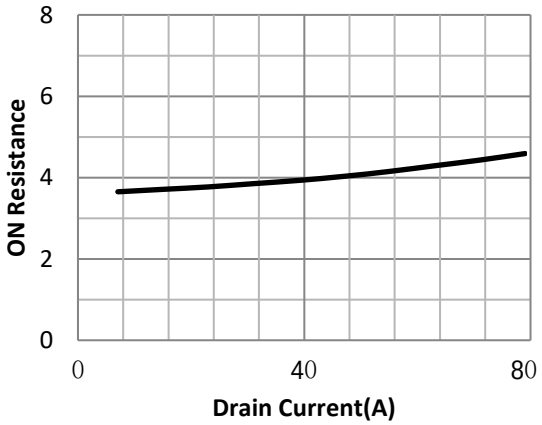


Fig.5 On-Resistance VS Drain Current

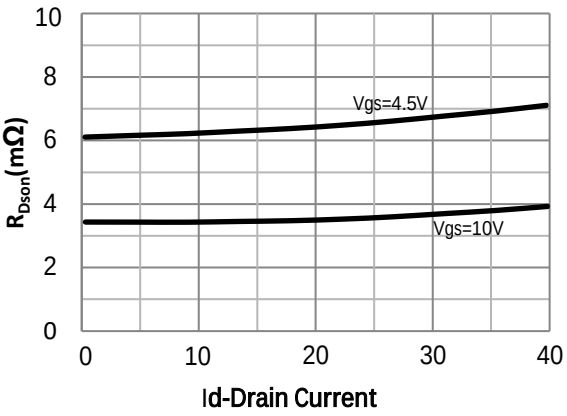


Fig.6 On-Resistance V.S Junction Temperature

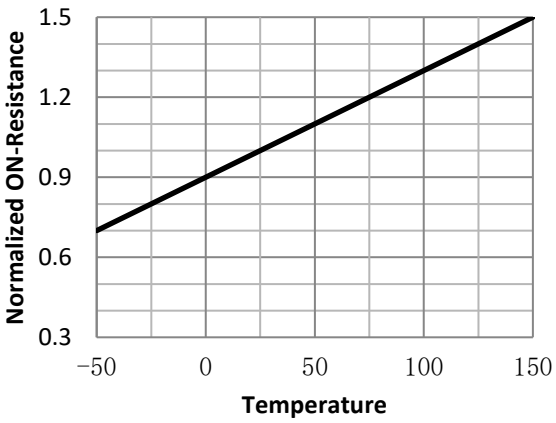


Fig.7 Switching Time Measurement Circuit

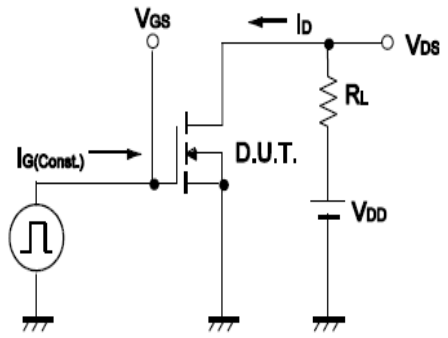


Fig.8 Gate Charge Waveform

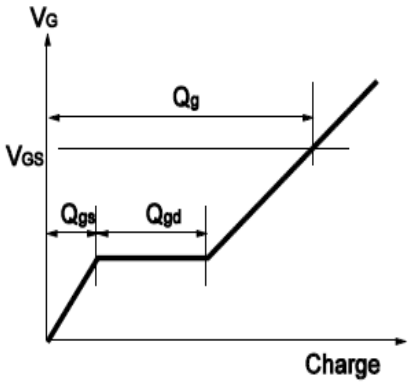


Fig.9 Switching Time Measurement Circuit

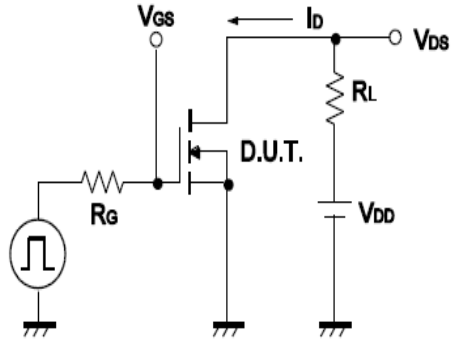


Fig.10 Gate Charge Waveform

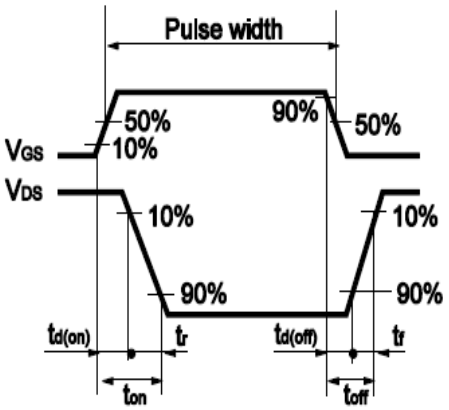


Fig.11 Avalanche Measurement Circuit

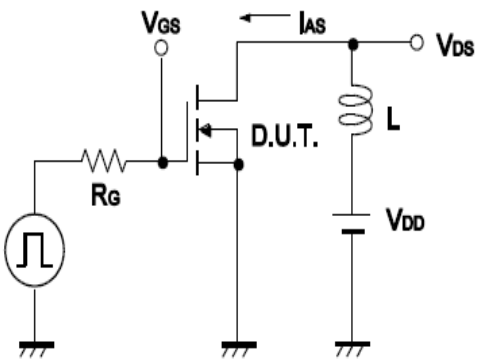
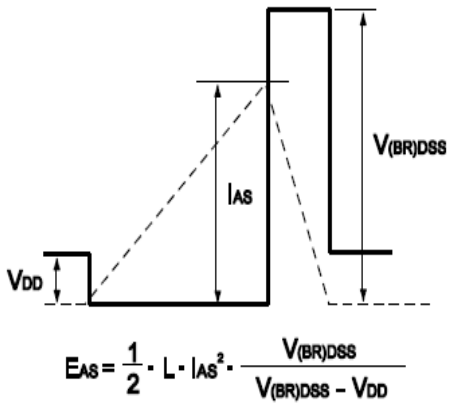
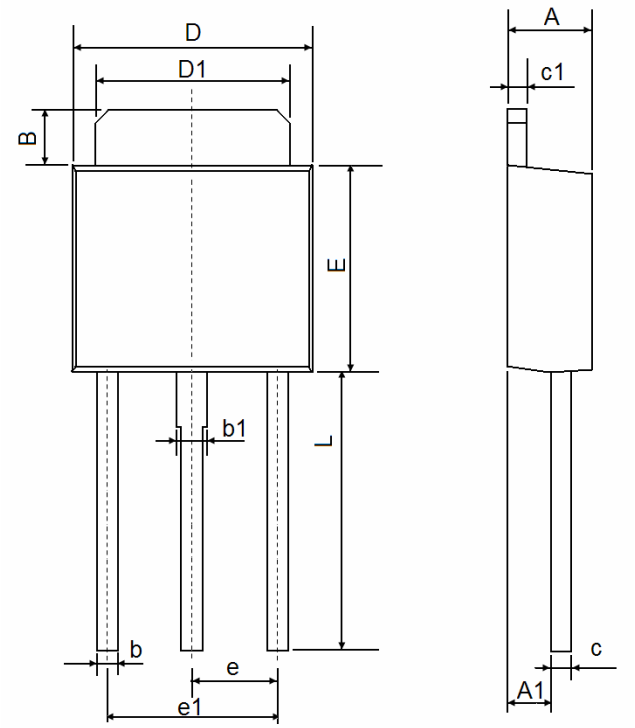


Fig.12 Avalanche Waveform



Package Information

TO-251



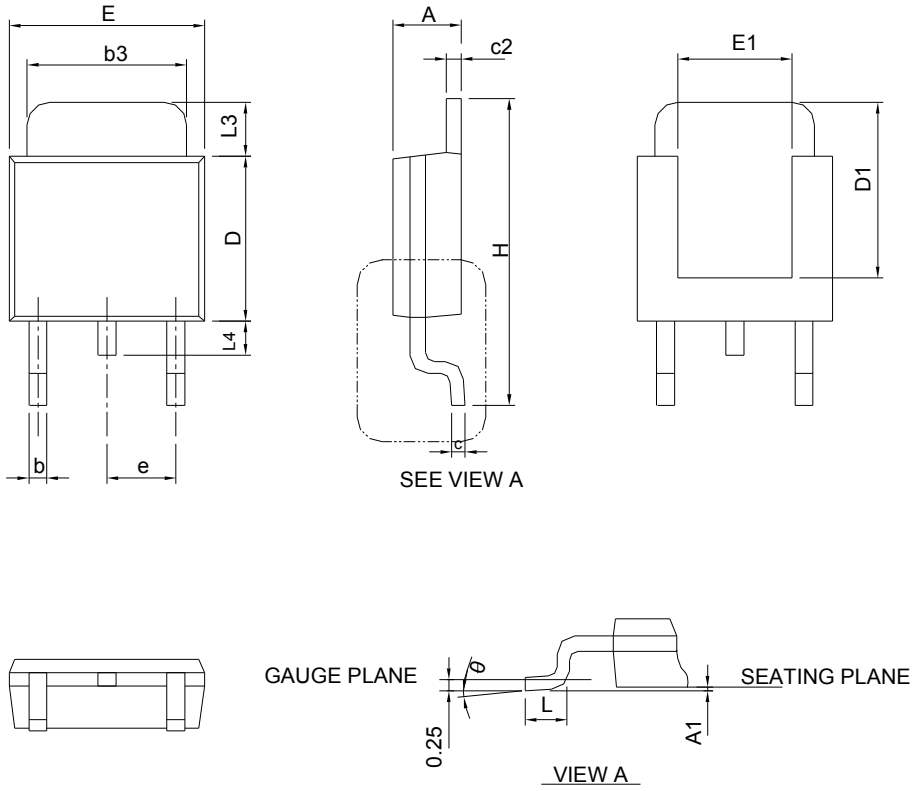
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	0.700	1.000	0.028	0.040
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	6.000	0.213	0.237
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	4.900	9.400	0.194	0.372

Notes

1. All dimensions are in millimeters.
2. Tolerance ±0.10mm (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exac

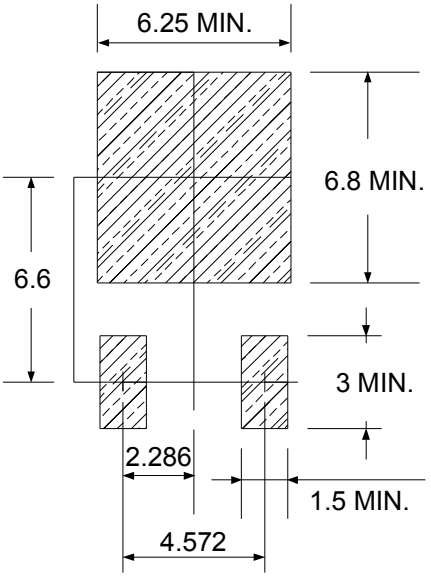
Package Information

TO-252



SYMBOL	TO-252			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1		0.13		0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4		1.02		0.040
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



UNIT: mm